TOSHIBA Transistor Silicon PNP Triple Diffused Type (PCT Process)

2SA940A

Power Amplifier Applications Vertical Output Applications

• Complementary to 2SC2073A

Maximum Ratings (Tc = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V_{CBO}	-150	V	
Collector-emitter voltage		V _{CEO}	-150	V	
Emitter-base voltage		V _{EBO}	-5	V	
Collector current		I _C	-1.5	Α	
Base current		Ι _Β	-0.5	А	
Collector power dissipation	Ta = 25°C	Pc	2.0	W	
	Tc = 25°C	FC	25		
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	

Unit: mm 10±0.3 03.2±0.2 2,7+0.2 0.75±0.15 1. BASE 2. COLLECTOR 3. EMITTER JEDEC JEITA SC-67 TOSHIBA 2-10R1A

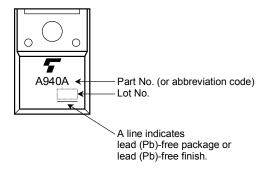
Weight: 1.7 g (typ.)

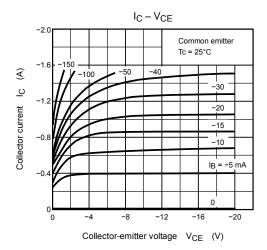
Electrical Characteristics (Tc = 25°C)

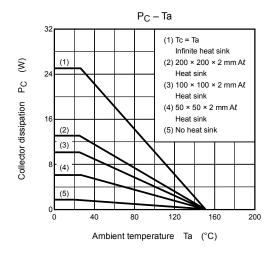
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = -120 V, I _E = 0	_	_	-10	μΑ
Emitter cut-off current	I _{EBO}	$V_{EB} = -5 \text{ V, } I_{C} = 0$	_	_	-10	μA
DC current gain	h _{FE}	$V_{CE} = -10 \text{ V}, I_{C} = -500 \text{ mA}$	40	75	140	
Collector-emitter saturation voltage	V _{CE (sat)}	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$	_	_	-1.5	V
Base-emitter voltage	V_{BE}	$V_{CE} = -10 \text{ V}, I_{C} = -500 \text{ mA}$	-0.65	-0.75	-0.85	V
Transition frequency	f _T	$V_{CE} = -10 \text{ V}, I_{C} = -500 \text{ mA}$	_	4	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = -10 V, I _E = 0, f = 1 MHz	_	55	_	pF

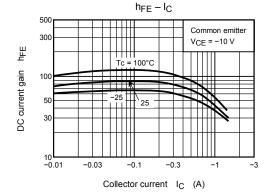
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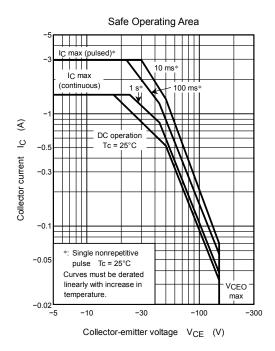
Marking

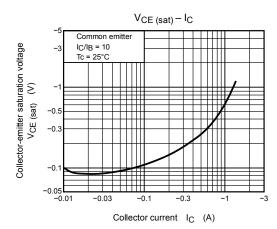












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